Contribution ID: **32** Type: **not specified**

On MCz SCSI after 24 GeV/c proton irradiation

Monday 2 June 2008 14:30 (20 minutes)

Several MCz diodes from the SMART production, of both n- and p-type, have been irradiated on the 24 GeV/c proton beam at CERN up to a fluence of 1.59 1015 neq.In the framework of a common RD50 research program, electrical characterization and TCT studies have been performed as a function of the annealing time. All irradiated samples show a clear double junction effect. Both annealing and TCT studies seem to indicate the occurrence of type inversion of p-type diodes at high fluences.

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Session Classification: Defect Engineering & Pad Detector Characterization I

Track Classification: Defect Engineering and Pad Detector Characterization